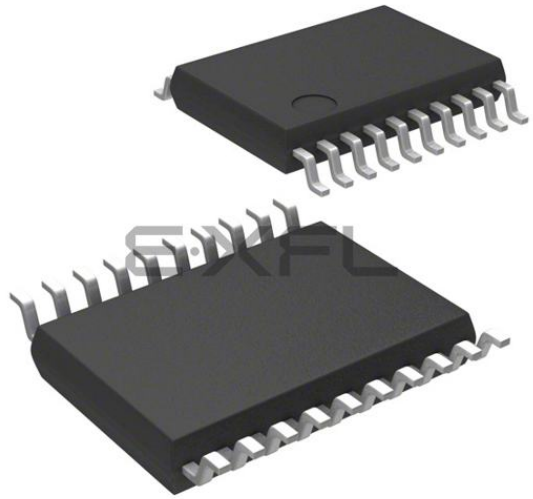

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	STM8
Core Size	8-Bit
Speed	16MHz
Connectivity	I²C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, IR, POR, PWM, WDT
Number of I/O	18
Program Memory Size	4KB (4K x 8)
Program Memory Type	FLASH
EEPROM Size	256 x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-TSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-TSSOP
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm8l151f2p6

3.10 System configuration controller and routing interface

The system configuration controller provides the capability to remap some alternate functions on different I/O ports. TIM4 and ADC1 DMA channels can also be remapped.

The highly flexible routing interface controls the routing of internal analog signals to ADC1, COMP1, COMP2, and the internal reference voltage V_{REFINT}. It also provides a set of registers for efficiently managing the charge transfer acquisition sequence (*Section 3.11: Touch sensing*).

3.11 Touch sensing

Low-density STM8L151x2/3 devices provide a simple solution for adding capacitive sensing functionality to any application. Capacitive sensing technology is able to detect finger presence near an electrode which is protected from direct touch by a dielectric (example, glass, plastic). The capacitive variation introduced by a finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle. It consists of charging the electrode capacitance and then transferring a part of the accumulated charges into a sampling capacitor until the voltage across this capacitor has reached a specific threshold. In low-density STM8L15xxx devices, the acquisition sequence is managed either by software or by hardware and it involves analog I/O groups, the routing interface, and timers.Reliable touch sensing solutions can be quickly and easily implemented using the free STM8 Touch Sensing Library.

3.12 Timers

Low-density STM8L151x2/3devices contain two 16-bit general purpose timers (TIM2 and TIM3) and one 8-bit basic timer (TIM4).

All the timers can be served by DMA1.

Table 2 compares the features of the advanced control, general-purpose and basic timers.

Table 2. Timer feature comparison

Timer	Counter resolution	Counter type	Prescaler factor	DMA1 request generation	Capture/compare channels	Complementary outputs
TIM2	16-bit	up/down	Any power of 2 from 1 to 128	Yes	2	None
TIM3						
TIM4	8-bit	up	Any power of 2 from 1 to 32768		0	

Table 4. Low-density STM8L151x2/3 pin description (continued)

Pin number					Pin name	Type	I/O level	Input			Output			Main function (after reset)	Default alternate function
LQFP48	UFQFPN32	UFQFPN28	UFQFPN20	TSSOP20				floating	wpu	Ext. interrupt	High sink/source	OD	PP		
25	14	13	8	11	PB1/TIM3_CH1/ ADC1_IN17/ COMP1_INP	I/O	-	**X**	X	X	HS	X	X	**Port B1**	Timer 3 - channel1/ ADC1_IN17/ Comparator1 positive input
26	15	14	9	12	PB2/ TIM2_CH2/ ADC1_IN16/ COMP1_INP	I/O	-	**X**	X	X	HS	X	X	**Port B2**	Timer 2 - channel2 ADC1_IN16/ Comparator1 positive input
27	16	15	10	13	PB3/TIM2_ETR/ ADC1_IN15/RTC_ALARM[4]/ COMP1_INP	I/O	-	**X**	X	X	HS	X	X	**Port B3**	Timer 2 - external trigger / ADC1_IN15 / RTC_ALARM [4]/Comparator1 positive input
28	17	16	11	14	PB4[3]/SPI1_NSS/ ADC1_IN14/ COMP1_INP	I/O	-	**X**	X	X	HS	X	X	**Port B4**	SPI master/slave select / ADC1_IN14/ Comparator1 positive input
29	18	17	12	15	PB5/SPI_SCK/ /ADC1_IN13/ COMP1_INP	I/O	-	**X**	X	X	HS	X	X	**Port B5**	[SPI clock] / ADC1_IN13/ Comparator 1 positive input
30	19	18	13	16	PB6/SPI1_MOSI/ ADC1_IN12/ COMP1_INP	I/O	-	**X**	X	X	HS	X	X	**Port B6**	SPI master out/ slave in / ADC1_IN12/ Comparator1 positive input
31	20	19	14	17	PB7/SPI1_MISO/ ADC1_IN11/ COMP1_INP	I/O	-	**X**	X	X	HS	X	X	**Port B7**	SPI1 master in-slave out/ ADC1_IN11/ Comparator1 positive input
37	25	21	15	18	PC0/I2C_SDA	I/O	FT	**X**		X		T[5]		**Port C0**	I2C data
38	26	22	16	19	PC1/I2C_SCL	I/O	FT	**X**		X		T[5]		**Port C1**	I2C clock
41	27	23	-	-	PC2/USART_RX/ADC 1_IN6/ COMP1_INP	I/O	-	**X**	X	X	HS	X	X	**Port C2**	USART receive / ADC1_IN6/ Comparator1 positive input
42	28	24	-	-	PC3/USART_TX/ ADC1_IN5/ COMP1_INP/ COMP2_INM	I/O	-	**X**	X	X	HS	X	X	**Port C3**	USART transmit / ADC1_IN5/ Comparator1 positive input/Comparator 2 negative input

Table 8. General hardware register map (continued)

Address	Block	Register label	Register name	Reset status
0x00 5280	TIM3	TIM3_CR1	TIM3 control register 1	0x00
0x00 5281		TIM3_CR2	TIM3 control register 2	0x00
0x00 5282		TIM3_SMCR	TIM3 Slave mode control register	0x00
0x00 5283		TIM3_ETR	TIM3 external trigger register	0x00
0x00 5284		TIM3_DER	TIM3 DMA1 request enable register	0x00
0x00 5285		TIM3_IER	TIM3 interrupt enable register	0x00
0x00 5286		TIM3_SR1	TIM3 status register 1	0x00
0x00 5287		TIM3_SR2	TIM3 status register 2	0x00
0x00 5288		TIM3_EGR	TIM3 event generation register	0x00
0x00 5289		TIM3_CCMR1	TIM3 Capture/Compare mode register 1	0x00
0x00 528A		TIM3_CCMR2	TIM3 Capture/Compare mode register 2	0x00
0x00 528B		TIM3_CCER1	TIM3 Capture/Compare enable register 1	0x00
0x00 528C		TIM3_CNTRH	TIM3 counter high	0x00
0x00 528D		TIM3_CNTRL	TIM3 counter low	0x00
0x00 528E		TIM3_PSCR	TIM3 prescaler register	0x00
0x00 528F		TIM3_ARRH	TIM3 Auto-reload register high	0xFF
0x00 5290		TIM3_ARRL	TIM3 Auto-reload register low	0xFF
0x00 5291		TIM3_CCR1H	TIM3 Capture/Compare register 1 high	0x00
0x00 5292		TIM3_CCR1L	TIM3 Capture/Compare register 1 low	0x00
0x00 5293		TIM3_CCR2H	TIM3 Capture/Compare register 2 high	0x00
0x00 5294		TIM3_CCR2L	TIM3 Capture/Compare register 2 low	0x00
0x00 5295		TIM3_BKR	TIM3 break register	0x00
0x00 5296		TIM3_OISR	TIM3 output idle state register	0x00
0x00 5297 to 0x00 52DF	Reserved area (72 byte)			

7 Option bytes

Option bytes contain configurations for device hardware features as well as the memory protection of the device. They are stored in a dedicated memory block.

All option bytes can be modified in ICP mode (with SWIM) by accessing the EEPROM address. See *Table 11* for details on option byte addresses.

The option bytes can also be modified ‘on the fly’ by the application in IAP mode, except for the ROP and UBC values which can only be taken into account when they are modified in ICP mode (with the SWIM).

Refer to the STM8L15x Flash programming manual (PM0054) and STM8 SWIM and Debug Manual (UM0470) for information on SWIM programming procedures.

Table 11. Option byte addresses

Addr.	Option name	Option byte No.	Option bits								Factory default setting
			7	6	5	4	3	2	1	0	
0x00 4800	Read-out protection (ROP)	OPT0	ROP[7:0]								0xAA
0x00 4802	UBC (User Boot code size)	OPT1	UBC[7:0]								0x00
0x00 4807	Reserved										0x00
0x00 4808	Independent watchdog option	OPT3 [3:0]	Reserved				WWDG_HALT	WWDG_HW	IWDG_HALT	IWDG_HW	0x00
0x00 4809	Number of stabilization clock cycles for HSE and LSE oscillators	OPT4	Reserved				LSECNT[1:0]		HSECNT[1:0]		0x00
0x00 480A	Brownout reset (BOR)	OPT5 [3:0]	Reserved				BOR_TH			BOR_ON	0x01
0x00 480B	Bootloader option bytes (OPTBL)	OPTBL [15:0]	OPTBL[15:0]								0x00
0x00 480C											0x00

Table 12. Option byte description

Option byte No.	Option description
OPT0	**ROP[7:0]** Memory readout protection (ROP) 0xAA: Disable readout protection (write access via SWIM protocol) Refer to Readout protection section in the STM8L15x and STM8L16x reference manual (RM0031).
OPT1	**UBC[7:0]** Size of the user boot code area 0x00: UBC is not protected. 0x01: Page 0 is write protected. 0x02: Page 0 and 1 reserved for the UBC and write protected. It covers only the interrupt vectors. 0x03: Page 0 to 2 reserved for UBC and write protected. 0x7F to 0xFF - All 128 pages reserved for UBC and write protected. The protection of the memory area not protected by the UBC is enabled through the MASS keys. Refer to User boot code section in the STM8L15x and STM8L16x reference manual (RM0031).
OPT2	Reserved
OPT3	**IWDG_HW:** Independent watchdog 0: Independent watchdog activated by software 1: Independent watchdog activated by hardware
	IWDG_HALT: Independent window watchdog off on Halt/Active-halt 0: Independent watchdog continues running in Halt/Active-halt mode 1: Independent watchdog stopped in Halt/Active-halt mode
	WWDG_HW: Window watchdog 0: Window watchdog activated by software 1: Window watchdog activated by hardware
	WWDG_HALT: Window window watchdog reset on Halt/Active-halt 0: Window watchdog stopped in Halt mode 1: Window watchdog generates a reset when MCU enters Halt mode
OPT4	**HSECNT**: Number of HSE oscillator stabilization clock cycles 0x00 - 1 clock cycle 0x01 - 16 clock cycles 0x10 - 512 clock cycles 0x11 - 4096 clock cycles
	LSECNT: Number of LSE oscillator stabilization clock cycles 0x00 - 1 clock cycle 0x01 - 16 clock cycles 0x10 - 512 clock cycles 0x11 - 4096 clock cycles Refer to *Table 31: LSE oscillator characteristics on page 74*.

Table 12. Option byte description (continued)

Option byte No.	Option description
OPT5	**BOR_ON**: 0: Brownout reset off 1: Brownout reset on
	BOR_TH[3:1]: Brownout reset thresholds. Refer to *Table 22* for details on the thresholds according to the value of BOR_TH bits.
OPTBL	**OPTBL[15:0]**: This option is checked by the boot ROM code after reset. Depending on content of addresses 00 480B, 00 480C and 0x8000 (reset vector) the CPU jumps to the bootloader or to the reset vector. Refer to the UM0560 bootloader user manual for more details.

8 Unique ID

STM8 devices feature a 96-bit unique device identifier which provides a reference number that is unique for any device and in any context. The 96 bits of the identifier can never be altered by the user.

The unique device identifier can be read in single bytes and may then be concatenated using a custom algorithm.

The unique device identifier is ideally suited:

- For use as serial numbers
- For use as security keys to increase the code security in the program memory while using and combining this unique ID with software cryptographic primitives and protocols before programming the internal memory.
- To activate secure boot processes

Table 13. Unique ID registers (96 bits)

Address	Content description	Unique ID bits							
		7	6	5	4	3	2	1	0
0x4926	X co-ordinate on the wafer	U_ID[7:0]							
0x4927		U_ID[15:8]							
0x4928	Y co-ordinate on the wafer	U_ID[23:16]							
0x4929		U_ID[31:24]							
0x492A	Wafer number	U_ID[39:32]							
0x492B	Lot number	U_ID[47:40]							
0x492C		U_ID[55:48]							
0x492D		U_ID[63:56]							
0x492E		U_ID[71:64]							
0x492F		U_ID[79:72]							
0x4930		U_ID[87:80]							
0x4931		U_ID[95:88]							

9.3 Operating conditions

Subject to general operating conditions for V_{DD} and T_A.

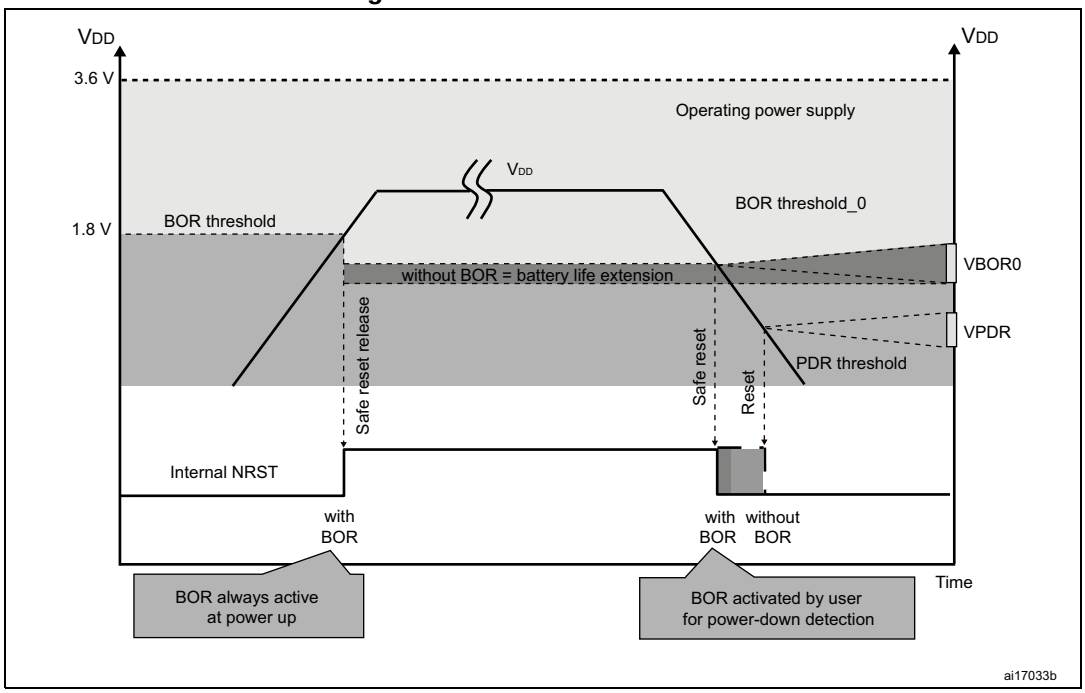
9.3.1 General operating conditions

Table 17. General operating conditions

Symbol	Parameter	Conditions		Min.	Max.	Unit
f_{SYSCLK}(1)	System clock frequency	1.65 V ≤ V_{DD} < 3.6 V		0	16	MHz
V_{DD}	Standard operating voltage	-		1.65(2)	3.6	V
V_{DDA}	Analog operating voltage	ADC1 not used	Must be at the same potential as V_{DD}	1.65(2)	3.6	V
		ADC1 used		1.8	3.6	V
P_D(3)	Power dissipation at T_A= 85 °C for suffix 3 and suffix 6 devices	LQFP48		-	288	mW
		UFQFPN32		-	288	
		UFQFPN28		-	250	
		UFQFPN20		-	196	
		TSSOP20		-	181	
	Power dissipation at T_A= 125 °C for suffix 3 devices	LQFP48		-	77	
		UFQFPN32		-	185	
		UFQFPN28		-	62	
		UFQFPN20		-	49	
		TSSOP20		-	45	
T_A	Temperature range	1.65 V ≤ V_{DD} < 3.6 V (6 suffix version)		-40	85	°C
		1.65 V ≤ V_{DD} < 3.6 V (3 suffix version)		-40	125	
T_J	Junction temperature range	-40 °C ≤ T_A < 85 °C (6 suffix version)		-40	105(4)	
		-40 °C ≤ T_A < 125 °C (3 suffix version)		-40	130(4)	

1. $f_{SYSCLK} = f_{CPU}$
2. 1.8 V at power-up, 1.65 V at power-down if BOR is disabled
3. To calculate $P_{Dmax}(T_A)$, use the formula $P_{Dmax}=(T_{Jmax} - T_A)/\Theta_{JA}$ with T_{Jmax} in this table and Θ_{JA} in “Thermal characteristics” table.
4. T_J max is given by the test limit. Above this value, the product behavior is not guaranteed.

Figure 11. POR/BOR thresholds



9.3.3 Supply current characteristics

Total current consumption

The MCU is placed under the following conditions:

- All I/O pins in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled except if explicitly mentioned.

In the following table, data is based on characterization results, unless otherwise specified.

Subject to general operating conditions for V_{DD} and T_A.

In the following table, data is based on characterization results, unless otherwise specified.

Table 21. Total current consumption and timing in Low power run mode at V_{DD} = 1.65 V to 3.6 V

Symbol	Parameter	Conditions[1][2]			Typ	Max	Unit
$I_{DD(LPR)}$	Supply current in Low power run mode	LSI RC osc. (at 38 kHz)	all peripherals OFF	T_A = -40 °C to 25 °C	5.1	5.4	µA
				T_A = 55 °C	5.7	6	
				T_A = 85 °C	6.8	7.5	
				T_A = 105 °C	9.2	10.4	
				T_A = 125 °C	13.4	16.6	
			with TIM2 active[3]	T_A = -40 °C to 25 °C	5.4	5.7	
				T_A = 55 °C	6.0	6.3	
				T_A = 85 °C	7.2	7.8	
				T_A = 105 °C	9.4	10.7	
				T_A = 125 °C	13.8	17	
		LSE [4] external clock (32.768 kHz)	all peripherals OFF	T_A = -40 °C to 25 °C	5.25	5.6	
				T_A = 55 °C	5.67	6.1	
				T_A = 85 °C	5.85	6.3	
				T_A = 105 °C	7.11	7.6	
				T_A = 125 °C	9.84	12	
			with TIM2 active [3]	T_A = -40 °C to 25 °C	5.59	6	
				T_A = 55 °C	6.10	6.4	
				T_A = 85 °C	6.30	7	
				T_A = 105 °C	7.55	8.4	
				T_A = 125 °C	10.1	15	

1. No floating I/Os
2. T_A > 85 °C is valid only for devices with suffix 3 temperature range.
3. Timer 2 clock enabled and counter running
4. Oscillator bypassed (LSEBYP = 1 in CLK_ECKCR). When configured for external crystal, the LSE consumption ($I_{DD\ LSE}$) must be added. Refer to *Table 31*

In the following table, data is based on characterization results, unless otherwise specified.

Table 22. Total current consumption in Low power wait mode at V_{DD} = 1.65 V to 3.6 V

Symbol	Parameter	Conditions(1)(2)			Typ	Max	Unit
$I_{DD(LPW)}$	Supply current in Low power wait mode	LSI RC osc. (at 38 kHz)	all peripherals OFF	T_A = -40 °C to 25 °C	3	3.3	µA
				T_A = 55 °C	3.3	3.6	
				T_A = 85 °C	4.4	5	
				T_A = 105 °C	6.7	8	
				T_A = 125 °C	11	14	
			with TIM2 active(3)	T_A = -40 °C to 25 °C	3.4	3.7	
				T_A = 55 °C	3.7	4	
				T_A = 85 °C	4.8	5.4	
				T_A = 105 °C	7	8.3	
				T_A = 125 °C	11.3	14.5	
		LSE external clock(4) (32.768 kHz)	all peripherals OFF	T_A = -40 °C to 25 °C	2.35	2.7	
				T_A = 55 °C	2.42	2.82	
				T_A = 85 °C	3.10	3.71	
				T_A = 105 °C	4.36	5.7	
				T_A = 125 °C	7.20	11	
			with TIM2 active (3)	T_A = -40 °C to 25 °C	2.46	2.75	
				T_A = 55 °C	2.50	2.81	
				T_A = 85 °C	3.16	3.82	
				T_A = 105 °C	4.51	5.9	
				T_A = 125 °C	7.28	11	

1. No floating I/Os.
2. T_A > 85 °C is valid only for devices with suffix 3 temperature range.
3. Timer 2 clock enabled and counter is running.
4. Oscillator bypassed (LSEBYP = 1 in CLK_ECKCR). When configured for external crystal, the LSE consumption ($I_{DD\ LSE}$) must be added. Refer to *Table 31*.

In the following table, data is based on characterization results, unless otherwise specified.

Table 23. Total current consumption and timing in Active-halt mode at V_{DD} = 1.65 V to 3.6 V

Symbol	Parameter	Conditions (1)(2)		Typ	Max	Unit
$I_{DD(AH)}$	Supply current in Active-halt mode	LSI RC (at 38 kHz)	T_A = -40 °C to 25 °C	0.9	2.1	µA
			T_A = 55 °C	1.2	3	
			T_A = 85 °C	1.5	3.4	
			T_A = 105 °C	2.6	6.6	
			T_A = 125 °C	5.1	12	
		LSE external clock (32.768 kHz) (3)	T_A = -40 °C to 25 °C	0.5	1.2	
			T_A = 55 °C	0.62	1.4	
			T_A = 85 °C	0.88	2.1	
			T_A = 105 °C	2.1	4.85	
			T_A = 125 °C	4.8	11	
$I_{DD(WUFAH)}$	Supply current during wakeup time from Active-halt mode (using HSI)	-	-	2.4	-	mA
$t_{WU\_HSI(AH)}$ (4)(5)	Wakeup time from Active-halt mode to Run mode (using HSI)	-	-	4.7	7	µs
$t_{WU\_LSI(AH)}$ (4) (5)	Wakeup time from Active-halt mode to Run mode (using LSI)	-	-	150	-	µs

1. No floating I/O, unless otherwise specified.
2. T_A > 85 °C is valid only for devices with suffix 3 temperature range.
3. Oscillator bypassed (LSEBYP = 1 in CLK_ECKCR). When configured for external crystal, the LSE consumption ($I_{DD\ LSE}$) must be added. Refer to *Table 31*
4. Wakeup time until start of interrupt vector fetch.
The first word of interrupt routine is fetched 4 CPU cycles after t_{WU}.
5. ULP=0 or ULP=1 and FWU=1 in the PWR_CSR2 register.

Table 24. Typical current consumption in Active-halt mode, RTC clocked by LSE external crystal

Symbol	Parameter	Condition(1)		Typ	Unit
$I_{DD(AH)}$ (2)	Supply current in Active-halt mode	V_{DD} = 1.8 V	LSE	1.15	µA
			LSE/32(3)	1.05	
		V_{DD} = 3 V	LSE	1.30	
			LSE/32(3)	1.20	
		V_{DD} = 3.6 V	LSE	1.45	
			LSE/32(3)	1.35	

1. No floating I/O, unless otherwise specified.
2. Based on measurements on bench with 32.768 kHz external crystal oscillator.
3. RTC clock is LSE divided by 32.

9.3.6 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC1 error, out of spec current injection on adjacent pins or other functional failure (for example reset, oscillator frequency deviation, etc.).

The test results are given in the following table.

Table 36. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on true open-drain pins (PC0 and PC1)	-5	+0	mA
	Injected current on all five-volt tolerant pins	-5	+0	
	Injected current on all 3.6 V tolerant pins	-5	+0	
	Injected current on any other pin	-5	+5	

9.3.7 I/O port pin characteristics

General characteristics

Subject to general operating conditions for V_{DD} and T_A unless otherwise specified. All unused pins must be kept at a fixed voltage: using the output mode of the I/O for example or an external pull-up or pull-down resistor.

Table 37. I/O static characteristics

Symbol	Parameter	Conditions(1)	Min	Typ	Max	Unit
V_{IL}	Input low level voltage(2)	Input voltage on true open-drain pins (PC0 and PC1)	V_{SS}-0.3	-	0.3 x V_{DD}	V
		Input voltage on any other pin	V_{SS}-0.3	-	0.3 x V_{DD}	
V_{IH}	Input high level voltage (2)	Input voltage on true open-drain pins (PC0 and PC1) with V_{DD} < 2 V	0.70 x V_{DD}	-	5.2	V
		Input voltage on true open-drain pins (PC0 and PC1) with $V_{DD} \geq 2$ V		-	5.5	
		Input voltage on any other pin	0.70 x V_{DD}	-	V_{DD}+0.3	
V_{hys}	Schmitt trigger voltage hysteresis (3)	I/Os	-	200	-	mV
		True open drain I/Os	-	200	-	
I_{lkg}	Input leakage current (4)	$V_{SS} \leq V_{IN} \leq V_{DD}$ High sink I/Os	-	-	50 (5)	nA
		$V_{SS} \leq V_{IN} \leq V_{DD}$ True open drain I/Os	-	-	200(5)	
		$V_{SS} \leq V_{IN} \leq V_{DD}$ PA0 with high sink LED driver capability	-	-	200(5)	
R_{PU}	Weak pull-up equivalent resistor(2)(6)	$V_{IN}=V_{SS}$	30	45	60	kΩ
C_{IO}	I/O pin capacitance	-	-	5	-	pF

1. V_{DD} = 3.0 V, T_A = -40 to 125 °C unless otherwise specified.
2. Data based on characterization results, not tested in production.
3. Hysteresis voltage between Schmitt trigger switching levels. Based on characterization results, not tested.
4. The max. value may be exceeded if negative current is injected on adjacent pins.
5. Not tested in production.
6. R_{PU} pull-up equivalent resistor based on a resistive transistor (corresponding I_{PU} current characteristics described in *Figure 23*).

NRST pin

Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 41. $\overline{\text{NRST}}$ pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}$	NRST input low level voltage (1)	-	V_{SS}	-	0.8	V
$V_{IH(NRST)}$	NRST input high level voltage (1)	-	1.4	-	V_{DD}	
$V_{OL(NRST)}$	NRST output low level voltage (1)	I_{OL} = 2 mA for 2.7 V ≤ V_{DD} ≤ 3.6 V	-	-	0.4	
		I_{OL} = 1.5 mA for V_{DD} < 2.7 V	-	-		
V_{HYST}	NRST input hysteresis(3)	-	10%V_{DD} (2)	-	-	mV
$R_{PU(NRST)}$	NRST pull-up equivalent resistor (1)	-	30	45	60	kΩ
$V_{F(NRST)}$	NRST input filtered pulse (3)	-	-	-	50	ns
$V_{NF(NRST)}$	NRST input not filtered pulse (3)	-	300	-	-	

1. Data based on characterization results, not tested in production.
2. 200 mV min.
3. Data guaranteed by design, not tested in production.

Figure 30. Typical NRST pull-up resistance R_{PU} vs V_{DD}

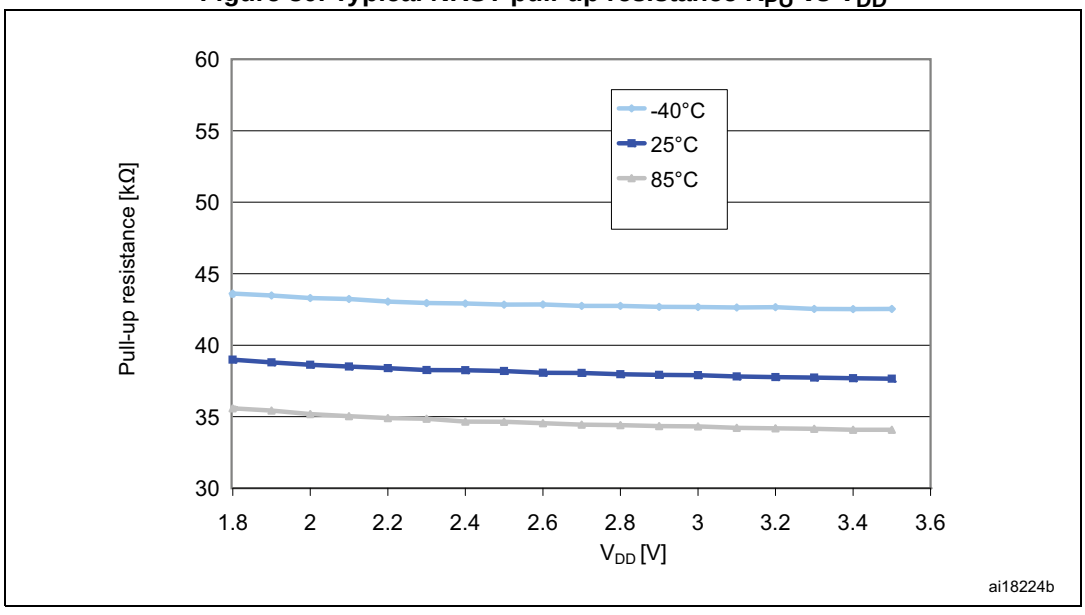


Figure 33. SPI1 timing diagram - slave mode and CPHA=0

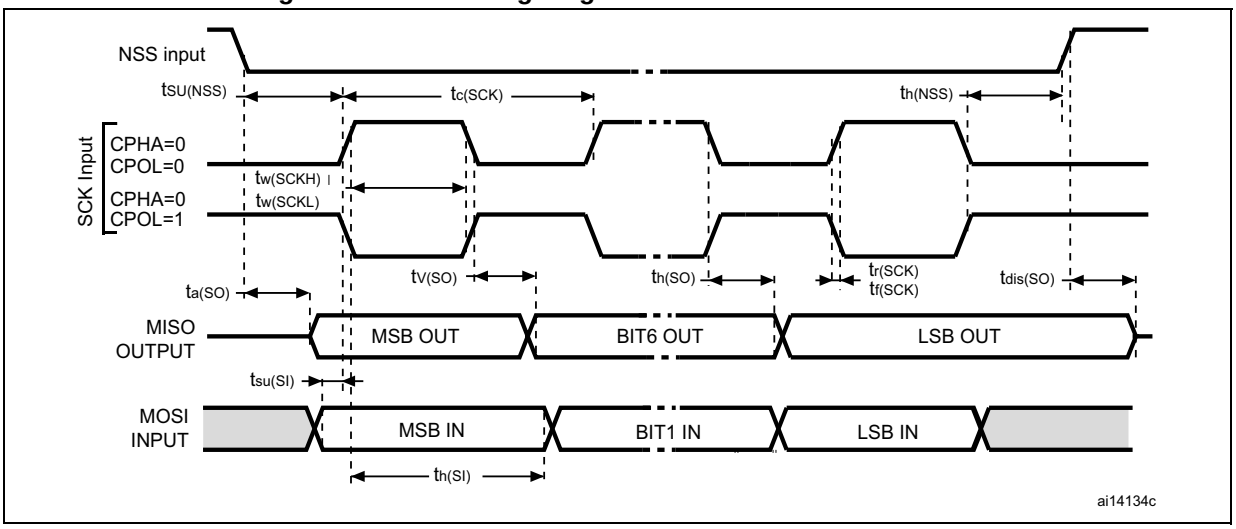
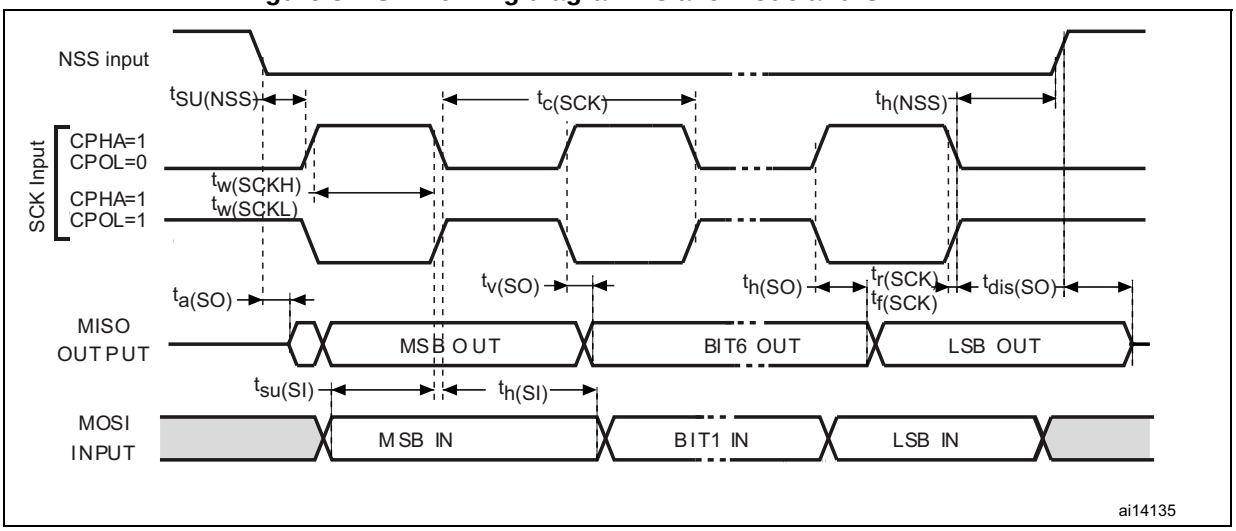


Figure 34. SPI1 timing diagram - slave mode and CPHA=1(1)



1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Table 48. ADC1 characteristics (continued)

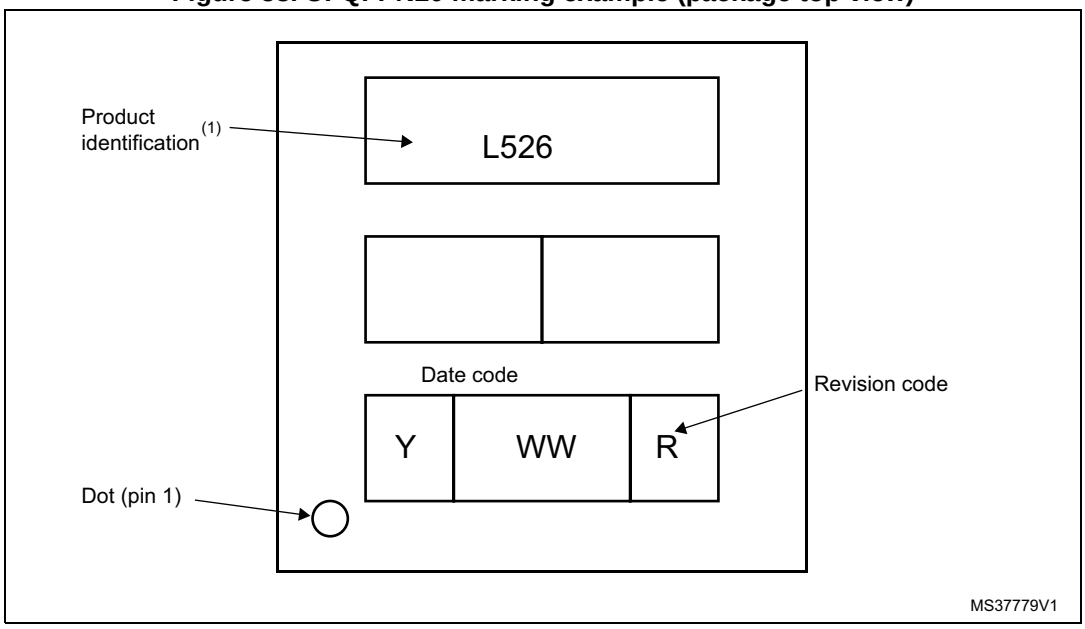
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_S	Sampling time	V_{AIN} on PF0 fast channel V_{DDA} < 2.4 V	0.43(4)(5)	-	-	µs
		V_{AIN} on PF0 fast channel 2.4 V ≤ V_{DDA}≤ 3.6 V	0.22(4)(5)	-	-	µs
		V_{AIN} on slow channels V_{DDA} < 2.4 V	0.86(4)(5)	-	-	µs
		V_{AIN} on slow channels 2.4 V ≤ V_{DDA}≤ 3.6 V	0.41(4)(5)	-	-	µs
t_{conv}	12-bit conversion time	-	12 + t_S			$1/f_{ADC1}$
		16 MHz	1(4)			µs
t_{WKUP}	Wakeup time from OFF state	-	-	-	3	µs
t_{IDLE}(6)	Time before a new conversion	T_A = +25 °C	-	-	1(7)	s
		T_A = +70 °C	-	-	20(7)	ms
		T_A = +125 °C	-	-	2(7)	ms
$t_{VREFINT}$	Internal reference voltage startup time	-	-	-	refer to *Table 44*	ms

1. The current consumption through V_{REF} is composed of two parameters:
   - one constant (max 300 µA)
   - one variable (max 400 µA), only during sampling time + 2 first conversion pulses.
   So, peak consumption is 300+400 = 700 µA and average consumption is 300 + [(4 sampling + 2) /16] x 400 = 450 µA at 1Msps
2. V_{REF-} or V_{DDA} must be tied to ground.
3. Guaranteed by design, not tested in production.
4. Minimum sampling and conversion time is reached for maximum Rext = 0.5 kΩ.
5. Value obtained for continuous conversion on fast channel.
6. The time between 2 conversions, or between ADC1 ON and the first conversion must be lower than t_{IDLE}.
7. The t_{IDLE} maximum value is ∞ on the “Z” revision code of the device.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Figure 53. UFQFPN20 marking example (package top view)

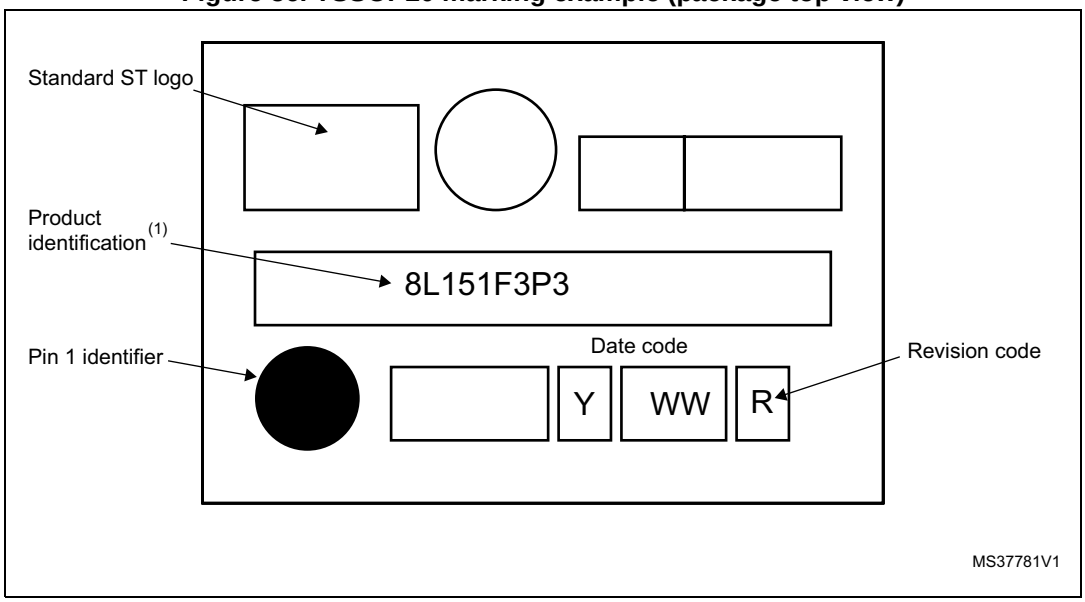


1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Figure 56. TSSOP20 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.